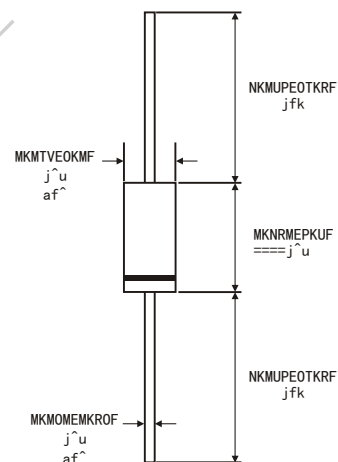


### FEATURES

- Metal-on-silicon junction
  - Low turn-on voltage
  - Ultrafast switching speed
  - Primarily intended for high level UHF mixers and ultrafast switching applications
- The diode is also available in the MiniMELF case with type designation LL29.
- High temperature soldering guaranteed: 260°C/10 seconds at terminals
  - Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



### DO-35



Dimensions in inches and (millimeters)

### MECHANICAL DATA

- Case: DO-35 glass case
- *Polarity:* color band denotes cathode end
- *Weight:* Approx. 0.13 gram

### ABSOLUTE RATINGS(LIMITING VALUES)

	Symbols	Value	Units
Peak Reverse Voltage	VRRM	5	V
Forward Continuous Current	IF	30	mA
Surge non repetitive forward current $t_p \leq 1s$	IFSM	60	mA
Junction and Storage temperature range	TSTG	-65 to +150	°C
	TJ	-65 to +150	°C
Maximum Lead Temperature for Soldering during 10s at 4mm from Case	TL	230	°C

### ELECTRICAL CHARACTERISTICS

	Symbols	Min.	Typ.	Max.	Unis
Reverse breakover voltage at $I_R=100\mu A$	VR	5			V
Leakage current at $V_R=1V$	IR			50	nA
Forward voltage drop at $I_F=10mA$ Test pulse: $t_p \leq 300\mu s$ $\delta < 2\%$	VF			0.55	V
Junction Capacitance at $V_R=0V$ , $f=1GHz$	CJ			1.0	pF
Thermal resistance	RθJA			400	K/W

# RATINGS AND CHARACTERISTIC CURVES

Figure 1. forward current versus forward voltage (typical values)

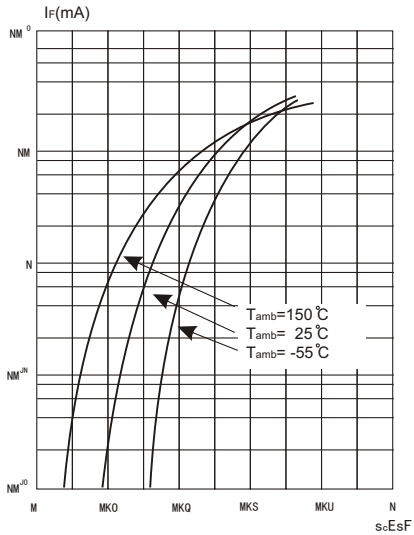


Figure 2. Capacitance  $C_J$  versus reverse applied voltage  $V_R$  (typical values)

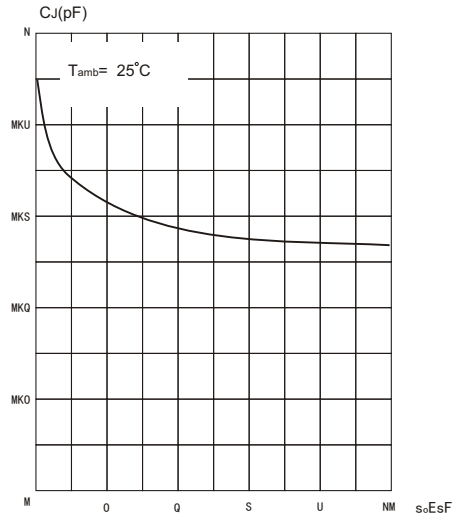


Figure 3. Reverse current versus ambient temperature

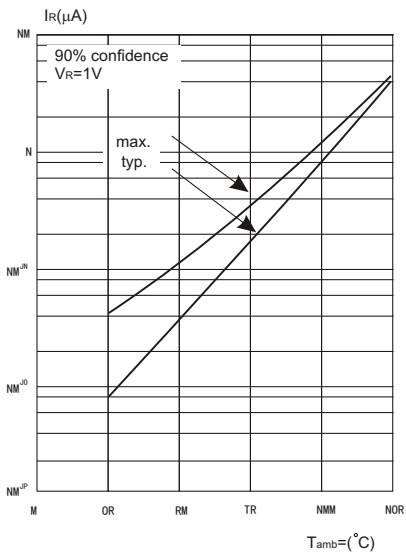


Figure 4. Reverse current versus continuous Reverse voltage (typical values)

